L Number	Hits	Search Text	DB	Time stamp
1	7	gate adj (oxide insulator) WITH diode near3 reverse adj breakdown	USPAT	2003/06/19 11:33
			US-PGPUB:	i
			EPO; JPO;	
			DERWENT:	
			IBM_TDB	
2	3774	((257/173,355-358,360-363) or (361/56,111)).CCLS.	USPAT,	2003/06/19 12:08
~	0,,,	(1207770,000 000,000 000) 01 (00 1100,1777)).0020	US-PGPUB	
3	200	(((257/173,355-358,360-363) or (361/56.111)).CCLS.) and @pd > "20030113"	USPAT:	2003/06/19 12:09
	200	(((23/11/3,333-330,300-303) of (30/130.111)).00E3.7 and wpd > 20030113	US-PGPUB	2003/00/13 12:03
	71	(((((257/173,355-358,360-363) or (361/56,111)).CCLS.) and @pd > "20030113") and	USPAT	2003/06/19 12:10
	7.1	((((237773,355-356,360-365) of (36756,177)).00E3.) and @pd > 20030173) and (68d electrostatic adj discharge)	USFAI	2003/00/13 12.10
5	2226	reverse adj breakdown	USPAT;	2003/06/19 12:14
	2326	reverse adjibreakdown		2003/00/19 12:14
ļ			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
6 [1168	breakdown near3 gate adj (oxide insulator)	USPAT;	2003/06/19 12:14
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
8	1257	(reverse adj breakdown) and input	USPAT;	2003/06/19 12:15
			US-PGPUB;	
			EPO; JPO;	
			DERWENT:	
			IBM_TDB	
9	45	core adj region and I/O adj region	USPAT;	2003/06/19 12:15
	40	i	US-PGPUB;	2000/00/10 12:10
			EPO: JPO:	
			DERWENT:	
			1	
	4040	A C M C I	IBM_TDB	2002/02/40 40 45
11	1313	protection with diode and cmos	USPAT;	2003/06/19 12:15
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
12	3523	input adj pad	USPAT;	2003/06/19 12:15
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
7	227	((reverse adj breakdown) and input) and (protection with diode)	USPAT;	2003/06/19 12:16
		, , , , , , , , , , , , , , , , , , , ,	US-PGPUB.	
			EPO; JPO;	
			DERWENT	
			IBM_TDB	
10	1	(protection with diode and cmos) and core adj region	USPAT;	2003/06/19 12:16
		The state of the s	US-PGPUB:	2000,00,10 12.10
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
13	40	(reverse adi breekdown) and (breekdown neer) gets adi (avide insulator))		2002/06/10 12:16
	40	(reverse adj breakdown) and (breakdown near3 gate adj (oxide insulator))	USPAT;	2003/06/19 12:16
14	74	////DE7/472 DEE DED DED DED DED DE /DE4/EE 444\\ OOL O\ Q \ "00000440"\\	US-PGPUB	2002/06/40 40 40
	71	(((((257/173,355-358,360-363) or (361/56,111)).CCLS.) and @pd > "20030113") and	USPAT;	2003/06/19 12:16
		(esd electrostatic adj discharge))	US-PGPUB	
15	332	((((reverse adj breakdown) and input) and (protection with diode)) ((reverse adj	USPAT;	2003/06/19 12:17
		breakdown) and input) (core adj region and I/O adj region) ((protection with diode and	US-PGPUB	1
		cmos) and core adj region) (protection with diode and cmos) (input adj pad) ((reverse	1	İ
	į	adj breakdown) and (breakdown near3 gate adj (oxide insulator)))		}
	İ	((((((257/173,355-358,360-363) or (361/56,111)) CCLS.) and @pd > "20030113") and	İ	ļ
	ŀ	(esd electrostatic adj discharge))) and @pd > "20030113"		1

16	139	(((((reverse adj breakdown) and input) and (protection with diode)) ((reverse adj	USPAT;	2003/06/19 12:17
		breakdown) and input) (core adj region and I/O adj region) ((protection with diode and	US-PGPUB	
		cmos) and core adj region) (protection with diode and cmos) (input adj pad) ((reverse		
		adj breakdown) and (breakdown near3 gate adj (oxide insulator)))		
		((((((257/173,355-358,360-363) or (361/56,111)) CCLS.) and @pd > "20030113") and		
		(esd electrostatic adj discharge))) and @pd > "20030113") not (input adj pad)		
17	267	((((257/173,355-358,360-363) or (361/56,111)) CCLS.) and @pd > "20030113")	USPAT;	2003/06/19 12:17
1		(((((((reverse adj breakdown) and input) and (protection with diode)) ((reverse adj	US-PGPUB	
1		breakdown) and input) (core adj region and I/O adj region) ((protection with diode and		
		cmos) and core adj region) (protection with diode and cmos) (input adj pad) ((reverse		
		adj breakdown) and (breakdown near3 gate adj (oxide insulator)))		
		((((((257/173,355-358,360-363) or (361/56,111)) CCLS.) and @pd > "20030113") and		
		(esd electrostatic adj discharge))) and @pd > "20030113") not (input adj pad))		